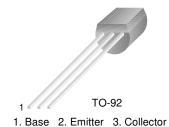


### KSP24

### **VHF Transistor**



## **NPN Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
I <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
I <sub>C</sub>	Collector Current	100	mA
l <sub>C</sub> P <sub>C</sub>	Collector Power Dissipation (T <sub>a</sub> =25°C)	350	mW
	Derate Above 25°C	2.8	mW/°C
TJ	Junction Temperature	135	°C
T <sub>STG</sub>	Storage Temperature	-55~150	°C
R <sub>TH</sub> (j-a)	Thermal Resistance, Junction to Ambient	357	°C/W

### **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>E</sub> =0	40			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =1mA, I <sub>B</sub> =0	30			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =10μA, I <sub>C</sub> =0	4.0			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =15V, I <sub>E</sub> =0			50	nA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =10V, I <sub>C</sub> =8mA	30			
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =10V, I <sub>C</sub> =8mA, f=100MHz	400	620		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		0.25	0.36	pF
G <sub>CE</sub>	Conversion Gain (213 to 45MHz)	V <sub>CC</sub> =20V, I <sub>C</sub> =8mA Oscillator Injection=150mV	19	24		dB
G <sub>CE</sub>	Conversion Gain (60 to 45MHz)	V <sub>CC</sub> =20V, I <sub>C</sub> =8mA Oscillator Injection=150mV	24	29		dB

## **Typical Characteristics**

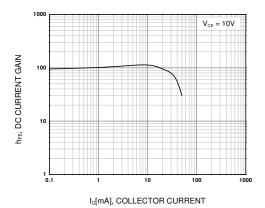


Figure 1. DC current Gain

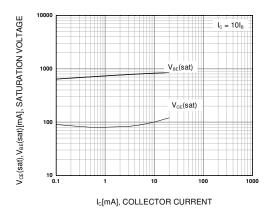


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

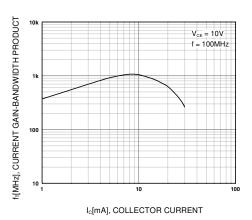


Figure 3. Current Gain Bandwidth Product

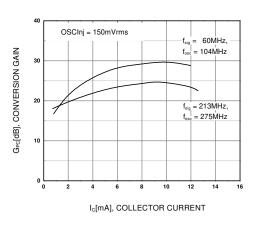


Figure 4. Conversion Gain versus Collector Current

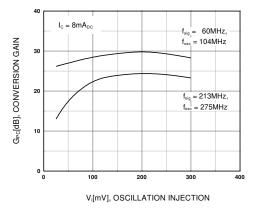


Figure 5. Conversion Gain versus Injection Level

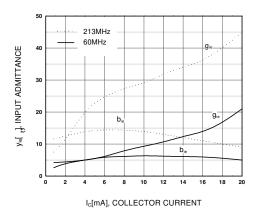


Figure 6. Input Admittance

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# Typical Characteristics (Continued)

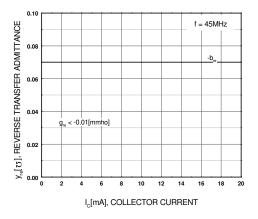


Figure 7. Reverse Transfer Admittance

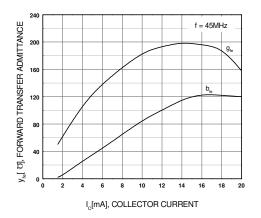


Figure 8. Forward Transfer Admittance

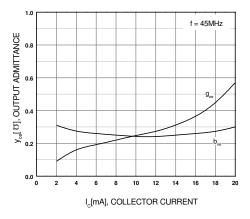
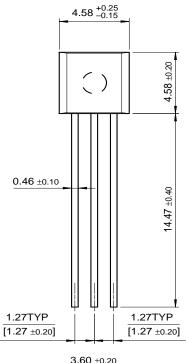


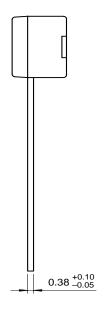
Figure 9. Output Admittance

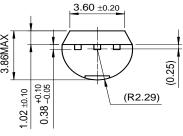
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# **Package Demensions**

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